

wherein  $f(\text{Hz})$  is a variable frequency of the high frequency power and wherein the plasma processing gas is a mixture gas of a reactant gas and an inert gas; and

*BC'* supplying high frequency power between the electrode and a holder to generate plasma between the electrode and the substrate on the basis of a plasma processing gas.

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Please add the following new claims:

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*BC'* --9. (New) The plasma processing method of claim 1, wherein the plasma processing method is one for performing etching on the substrate.

10. (New) The plasma processing method of claim 1, wherein the plasma processing method is one for performing surface treatment on the substrate.--

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